Nov. 2005

THE SPECIFICATION OF AlGaAs IR LED CHIP "IP4J-53"

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is P-side up. The peak wavelength is 850 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION			MIN.	TYP.	MAX.	UNIT
Forward Voltage	(Vf)	IF=20mA		1.4	1.6	V
Reverse Voltage	(Vr)	IR=10uA	5			V
Radiated Power[1)]	(Po)	IF=20mA	3.0			mW
Peak Wavelength	(λp)	IF=20mA	830	850	870	nm
Spectral Radiation Bandwidth	(Δλ)	IF=20mA		40		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 100 mA(DC)
Reverse Voltage : 5 V(IR=10uA)
Storage Temperature
while on mylar membrane : 0 to 40 deg. C
after removal from mylar membrane : -30 to 100 deg. C

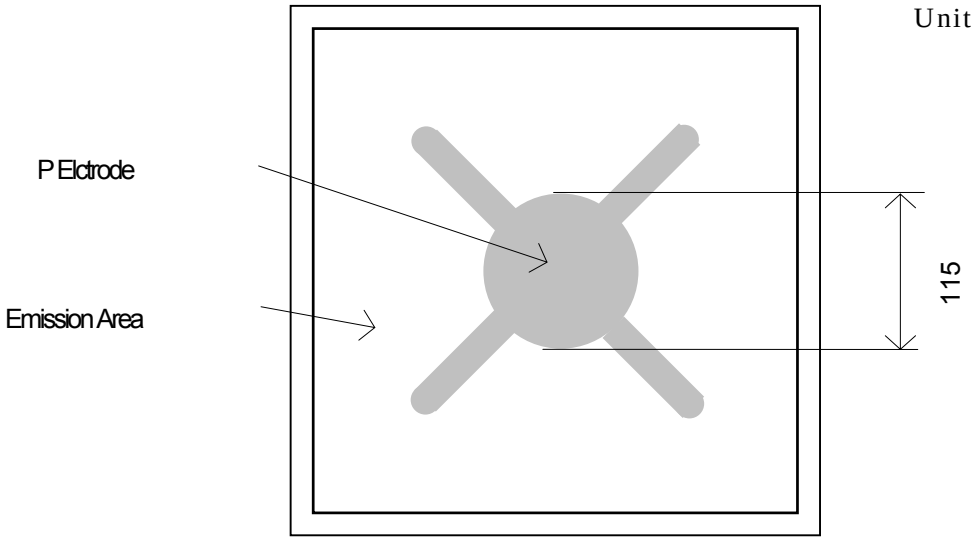
4. PHYSICAL CHRACTERISTICS AND STRUCTURE

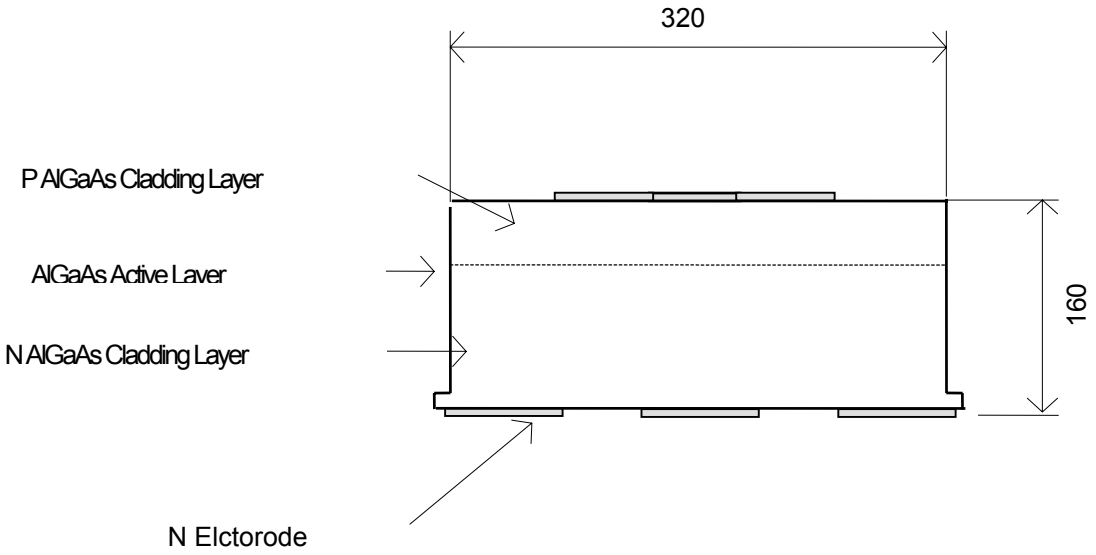
1) Material : AlGaAs
2) Structure : Double Hetero Structure
3) Junction Size : 0.320mmX0.320mm
4) Thickness : 0.160mm
5) Bond Pad Size : 0.115mm diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization : Gold Alloy

Physical Dimensions

Model IP4J-53

Unit: um





Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.